

14 Pin Dip, 3.3 & 5.0 Volt, HCMOS, Clipped Sinewave Precision TCXO/TCVCXO

Product Features

- Tight stability (0.5 ppm)
- 3.3 V and 5.0 V versions
- Wide frequency range 8-52 MHz
- · Low phase noise





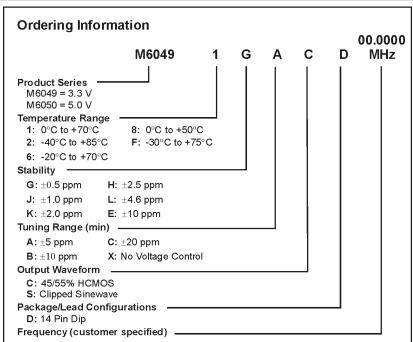
Product Description

MtronPTI's M6049/M6050 series of TCXO and TCVCXO's provide design engineers with a high stability in a reliable standard 14-DIP through-hole device. Tight stability of \pm 0.5 ppm is achievable utilizing MtronPTI's unique crystal compensation technology. Excellent phase noise (-152 dBc/Hz at 10kHz) is also exhibited by the M6049/M6050 series. HCMOS and clipped sinewave output types are available in frequencies from 8 MHz to 52 MHz.

Product Applications

The M6049/M6050 series is ideally suited for a wide range of applications such as SERDES, SONET, WiMAX, GSM, GPS, 3G & 4G, CDMA, Gig-E, and other wireless communications systems. The low power (< 10 mA) make the M6049/M6050 a good choice for use in battery back-up operated systems and other "green" related, power sensitive applications. The low phase noise allows the M6049/M6050 to be used as a reference oscillator for PLL circuits in RF synthesizers and digital transmission systems.

Product Ordering Information





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Performance Characteristics

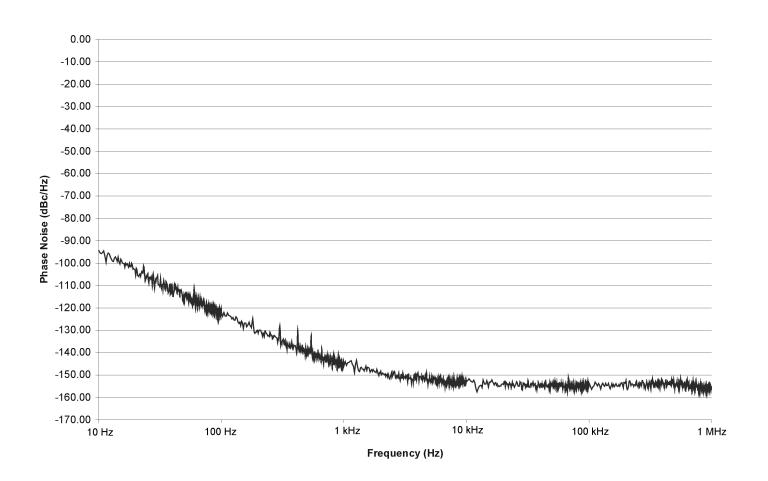
	Parameter	Symbol	Min.	Тур.	Max.	Units	Conditions/Notes
	Frequency Range	F₀	8		52	MHz	
	Operating Temperature	T _A	-40		+85	°C	See Ordering Information
	Storage Temperature	T_{STG}	-55		+125	°C	
	Frequency Tolerance @ +25°C		-1.0		+1.0	ppm	For TCXO only
	Frequency Stability						See Ordering Information
	Stability Vs. Reflow		-1.0		+1.0	ppm	
П	Frequency Vs. Supply			±0.2		ppm	For 10% supply voltage variation
	Frequency Vs. Load			±0.2		ppm	For 10% load variation
	Aging (First Year)		-1.0		+1.0	ppm	$F_0 \le 20 \text{ MHz}$
	Aging (First Year)		-2.0		+2.0	ppm	$F_0 \ge 20 \text{ MHz}$
	Aging (10 Year)		-3.0		+3.0	ppm	F ₀ ≤ 20 MHz (Includes first year)
	Aging (10 Year)		-5.0		+5.0	ppm	F ₀ ≥ 20 MHz (Includes first year)
၂ တ	Supply Voltage (V _S)		-5.0		+5.0	%	See Ordering Information
l o	Supply Current (I _D)			2.2	3.3	mA	HCMOS output at 13 MHz
äti				3.5	5.0	mA	HCMOS output at 26 MHz
Specifications				6.0	9.2	mA	HCMOS output at 52 MHz
l S	Output Logic Levels	V _{OL}			20	%V _S	$I_{OH}/I_{OL} = \pm 4 \text{ mA}, \text{ Vs} = +3.0 \text{ V}$
ြင္ပ	(HCMOS)	V_{OH}	80			%V₅	$I_{OH}/I_{OL} = \pm 4 \text{ mA}, \text{ Vs} = +3.0 \text{ V}$
ectrical	Output Logic Levels	V_{OL}	1.0			V_{pk-pk}	F _o < 40 MHz
ij	(Clipped Sinewave)	V_{OH}	0.8			$V_{\sf pk-pk}$	F _o > 40 MHz
<u> 6</u>	Waveform Symmetry		45		55	%	Ref. to 1/2 V _{S.} HCMOS only
ĮΞ	Rise/Fall Time				8	ns	Ref. 10% to 90%. HCMOS only
	Output Load			15		pF	HCMOS output
	Frequency Adjustment			See Orderir	ng Informa		Over Control Voltage Range
	Control Voltage Range		0.3		3.0	Volts	For $V_S = 3.3 \text{ V}$
			0.5		4.5	Volts	For $V_S = 5.0 \text{ V}$
	Input Leakage Current		-50		+50	μΑ	Pin 1
	Input Resistance		100			Kohm	Pin 1
	Linearity				10	%	
	Modulation Bandwidth		10			KHz	Pin 1, 20 MHz, min pull of ±10 ppm
	Phase Noise			-95		dBc/Hz	10 Hz Offset
	(Typical 10 MHz CMOS)			-125		dBc/Hz	100 Hz Offset
	,			-145		dBc/Hz	1 KHz Offset
				-152		dBc/Hz	10 KHz Offset
				-155		dBc/Hz	100 kHz Offset
Н							
Environmental	Observe Annual Office Control Office					1400	
Je.	Shock	MIL-STD-202, Method 213, Condition C				100 g	
l n	Vibration	ability EIAJ-STD-002					10 g from 10 to 2000 Hz
Įį.	Solderability						
[2]	Package					RoHS Compliant	
Ш							

HCMOS Load - see load circuit diagram #2. Clipped Sinewave Load - see load circuit diagram #7.

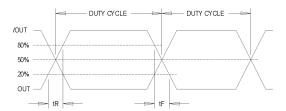


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Phase Noise Plot



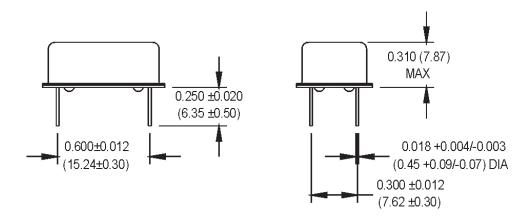
Output Waveform

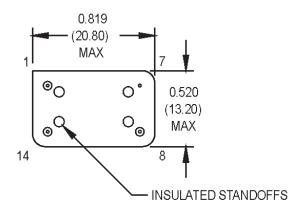




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Product Dimension & Pinout Information





PIN	FUNCTION	
1	N/C or Control Voltage	
7	Ground/Case	
8	Output	
14	14 +Vdd	

All dimensions in inches (mm).



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Handling Information

Although protection circuitry has been designed into the M6049/M6050 oscillator, proper precautions should be taken to avoid exposure to electrostatic discharge (ESD) during handling and mounting. MtronPTI utilizes a human-body model (HBM) and a charged-device model (CDM) for ESD-susceptibility testing and protection design evaluation. ESD voltage thresholds are dependent on the circuit parameters used to define the mode. Although no industry-wide standard has been adopted for the CDM, a standard HBM (resistance = 1500 Ω , capacitance = 100 pF) is widely used and therefore can be used for comparison purposes. The HBM ESD threshold presented here was obtained using these circuit parameters.

Model ESD Threshold, Minimum		Unit
Human Body	1500*	V
Charged Device	1500*	V

^{*} MIL-STD-833D, Method 3015, Class 1

ATTENTION Static Sensitive Devices Handle anly at Static Safe Work Stations

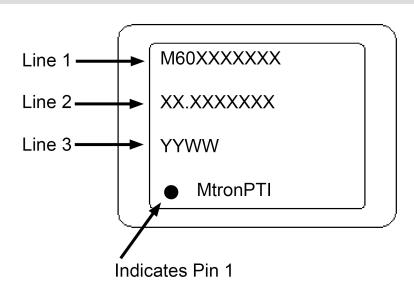
Quality Parameters

Environmental Specifications/Qualification Testing Performed on the M6049/M6050 TCXO/TCVCXO						
Test	Test Method	Test Condition				
Electrical Characteristics	Internal Specification	Per Specification				
Frequency vs. Temperature	Internal Specification	Per Specification				
Mechanical Shock	MIL-STD-202, Method 213, C	100 g, 6 ms				
Vibration	MIL-STD-202, Method 201-204	10 g from 10-2000 Hz				
Thermal Cycle	MIL-STD-883, Method 1010, B	-55 Deg. C to +125 Deg. C, 15 minute Dwell, 10 cycles				
Aging	Internal Specification	168 Hours at 105 Degrees C				
Gross Leak	MIL-STD-202, Method 112	30 Second Immersion				
Fine Leak	MIL-STD-202, Method 112	Must meet 1x10 ⁻⁸				
Solderability	MIL-STD-883, Method 2003	8 Hour Steam Age – Must Exhibit 95% coverage				
Resistance to Solvents	MIL-STD-883, Method 2015	Three 1 minute soaks				
Terminal Pull	MIL-STD-883, Method 2004, A	2 Pounds				
Lead Bend	MIL-STD-883, Method 2004, B1	1 Bending Cycle				
Physical Dimensions	MIL-STD-883, Method 2016	Per Specification				
Internal Visual	Internal Specification	Per Internal Specification				

Part Marking Guide

Line 1: Model Number Line 2: Frequency

Line 3: Date Code





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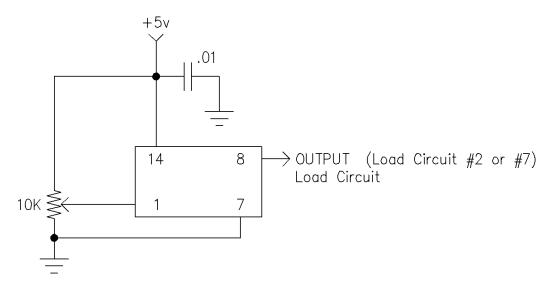
Maximum Wave Soldering Conditions:

Typical solder conditions for through hole crystals and oscillators: Per MIL-STD-202, Method 210 "Resistance to Soldering Heat", Condition C

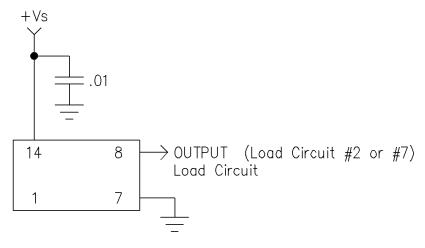
Wave solder with a solder bath temperature of $260^{\circ}\text{C} \pm 5^{\circ}\text{C}$ and an exposure time of 10 ±1 second. Preheat 1-4°C/s to within 100°C of solder temperature (25 ±6 mm/s).

Note: Exceeding these limits may damage the device.

Typical Test Circuit



Voltage Tune Option (TCVCXO)



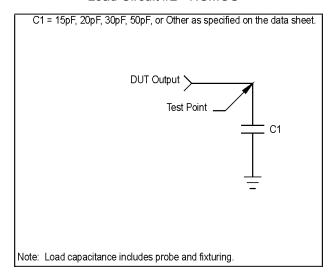
Non-Voltage Tune Option (TCXO)



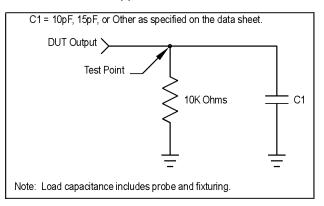
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Load Circuit

Load Circuit #2 - HCMOS



Load Circuit #7 - Clipped Sinewave TCXO/TCVCXO



Product Revision Table

Date	Revision	PCN Number	Details of Revision

For custom products or additional specifications contact our sales team at 800.762.8800 (toll free) or 605.665.9321

For more information on this product visit the MtronPTI website at www.mtronpti.com